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(54) Title: USE OF BUFFER MEMBERS DURING GROWTH OF SINGLE CRYSTAL SILICON INGOTS

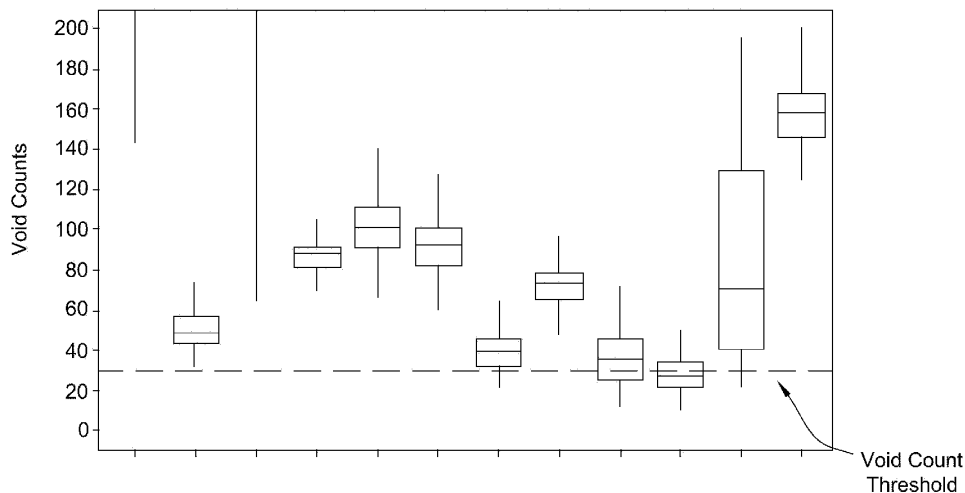


FIG. 4

(57) Abstract: Methods for producing single crystal silicon ingots by Continuous Czochralski (CCz) are disclosed. A batch of buffer members (e. g., quartz cullets) is added to an outer melt zone of the crucible assembly before the main body of the ingot is grown. In some embodiments, the ratio of the mass M of the batch of buffer members added to the melt to the time between adding the batch of buffer members to the melt and when the ingot main body begins to grow is controlled such that the ratio of M/T is greater than a threshold M/T.

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